

V_{RWM}	22	V
P_{PP}	40	W
V_{CL}	38	V

● Features

- Small mold type
- High reliability

● Application

- ESD Protection

● Structure

- Silicon Epitaxial Planar

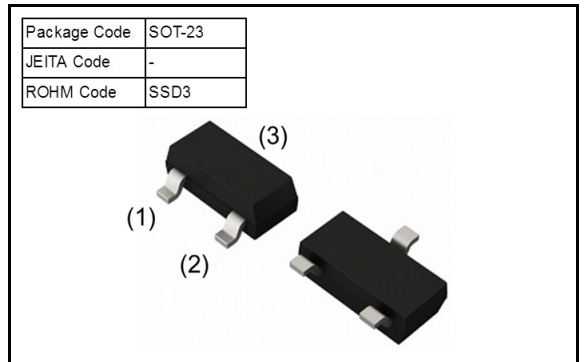
● Absolute Maximum Rating

Parameter	Symbol	Conditions	Min.	Max.	Unit	
Peak Pulse Power	P_{pp}	$t_p=10/1000\mu s$	-	40	W	
Power dissipation	P_D	on Glass-epoxy substrate	-	225	mW	
		on Alumina substrate	-	300	mW	
Junction temperature	T_j	-	-	150	°C	
Storage temperature	T_{stg}	-	-65	150	°C	
ESD capability	V_{ESD}	IEC61000-4-2*	Contact	-	30	kV
			Air	-	30	kV
		Machine model	-	2	kV	
		Human body model (MIL-STD-883)	-	8	kV	
		CDM (Charged device model)	-	500	V	

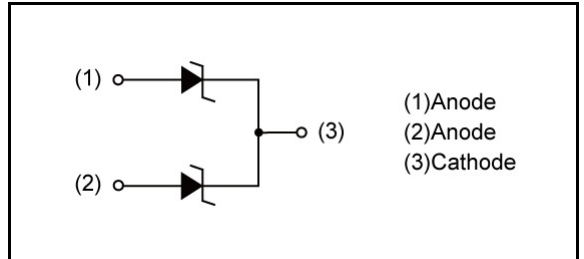
*IEC61000-4-2

C=150pF R=330Ω

● Outline



● Inner Circuit



● Packaging Specification

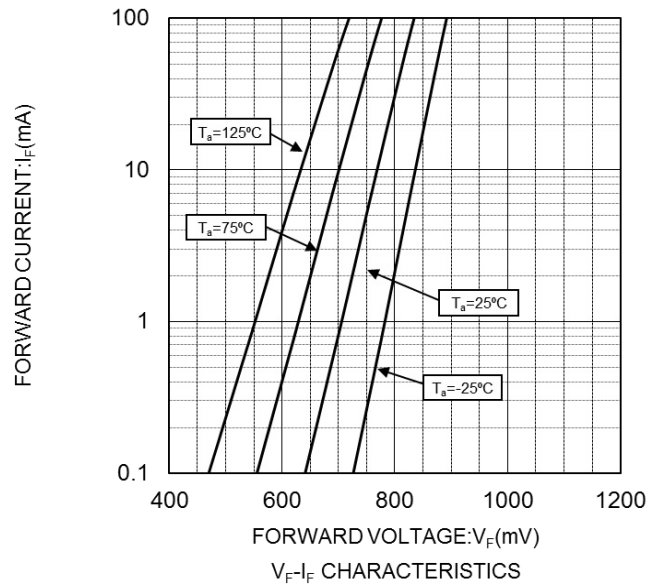
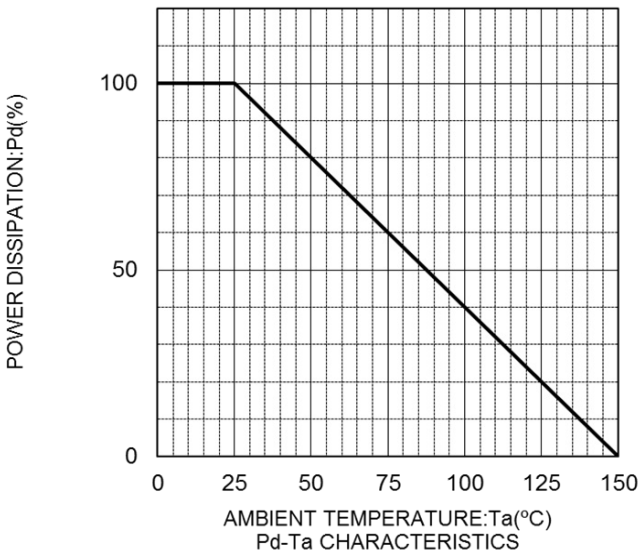
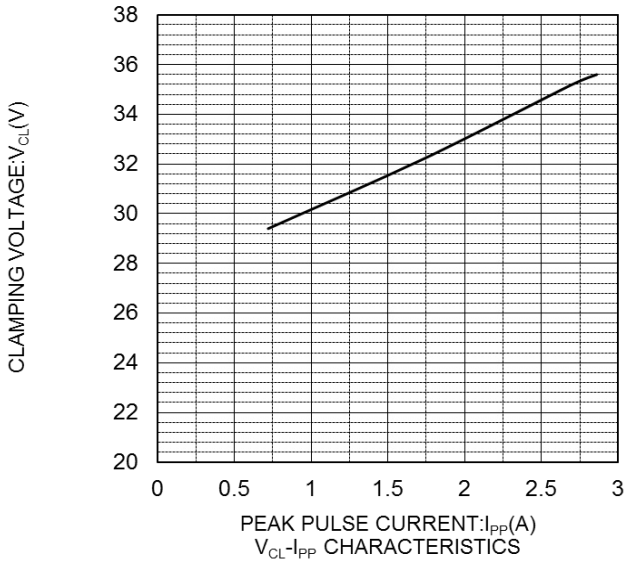
Packing	Embossed Tape
Reel Size(mm)	180
Taping Width(mm)	8
Basic Ordering Unit(pcs)	3000
Taping Code	T116
Marking	5T

● Characteristics

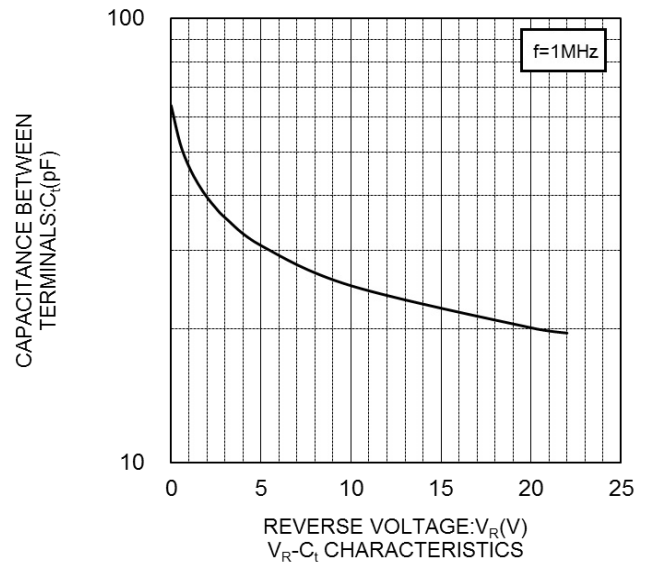
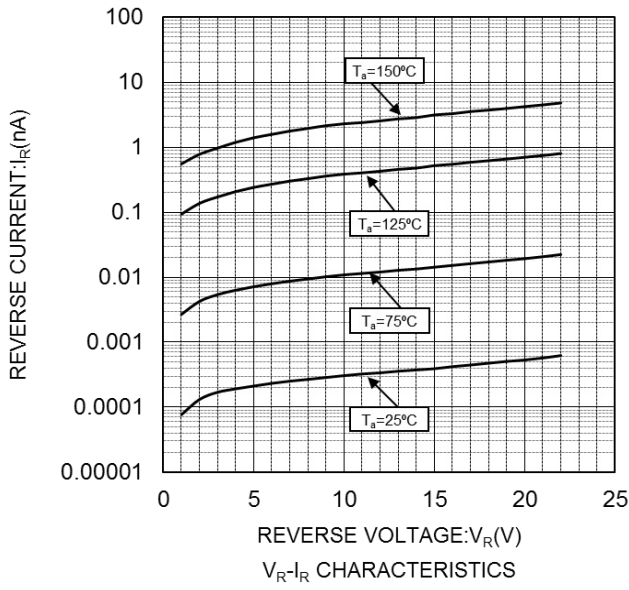
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Reverse Stand-off voltage	V_{RWM}	-	-	-	22	V
Breakdown voltage	V_{BR}	$I_T=1mA$	25.65	-	28.35	V
Reverse current	I_R	$V_R=22V$	-	-	50	nA
Clamping voltage	V_{CL}	$I_{pp}=1A, t_p=10/1000us$	-	-	38	V
Forward voltage	V_F	$I_F=200mA$	-	-	1.1	V

Breakdown voltage (V_{BR}) time is 40ms .

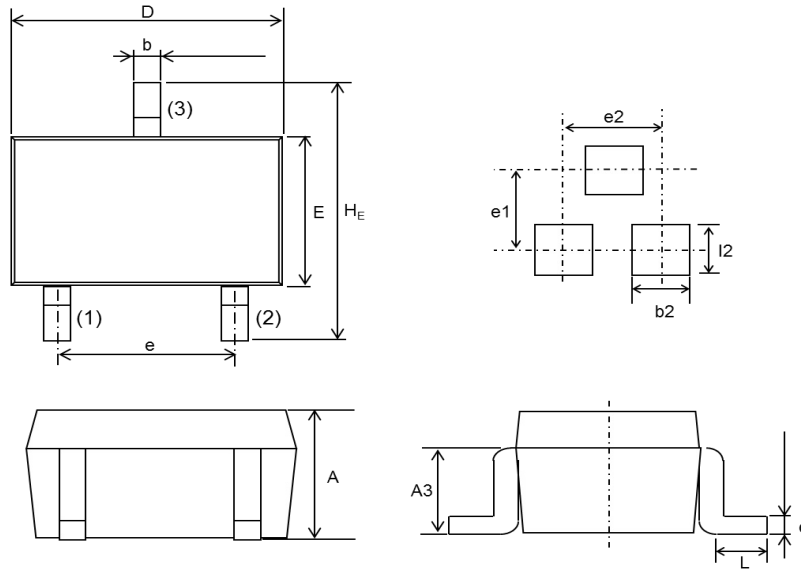
● Characteristic Curves



● Characteristic Curves



● Dimensions (SOT-23 SSD3)



DIM	Millimeters			Inches		
	Min.	Average	Max.	Min.	Average	Max.
A	0.85	0.95	1.15	0.033	0.037	0.045
A3	0.35	0.40	0.50	0.014	0.016	0.020
b	0.35	0.40	0.50	0.014	0.016	0.020
c	0.09	0.15	0.25	0.004	0.006	0.010
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.20	1.30	1.50	0.047	0.051	0.059
HE	2.20	2.40	2.60	0.087	0.094	0.102
L	0.20	-	-	0.008	-	-
e	1.70	1.90	2.10	0.067	0.075	0.083
l2	1.00	-	-	0.039	-	-
b2	0.80	-	-	0.031	-	-
e1	-	2.10	-	-	0.083	-
e2	-	1.90	-	-	0.075	-

● Taping (Unit:mm)

